

MS1506

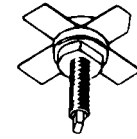
RF & MICROWAVE TRANSISTORS VHF MOBILE APPLICATIONS

Features

- 160 MHz
- 13.6 VOLTS
- P_{OUT} = 40 WATTS
- G_P = 9.0 dB MINIMUM
- COMMON EMITTER CONFIGURATION

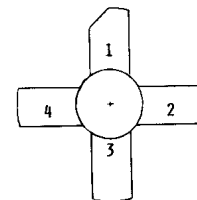
DESCRIPTION:

The MS1506 is a 13.6 volt Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications. The MS1506 utilizes an emitter ballasted die geometry to withstand severe load mismatch conditions.



.380 4LSTUD(M135)
epoxy sealed

PIN CONNECTION



1 collector
2 emitter

3 base
4 emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol			
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	8.0	A
P _{DISS}	Power Dissipation	70	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance	1.2	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)
STATIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
BV_{CES}	I_C = 15 mA	V_{BE} = 0 mA	36	---	---	V	
BV_{CEO}	I_C = 50 mA	I_B = 0 mA	18	---	---	V	
BV_{EBO}	I_E = 5 mA	I_C = 0 mA	4.0	---	---	V	
I_{CBO}	V_{CB} = 15 V	I_E = 0 mA	---	---	5	mA	
h_{FE}	V_{CE} = 5 V	I_C = 250 mA	20	---	200	---	

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 160 MHz	P_{IN} = 5.0 W	V_{CE} = 13.6 V	40	---	---	W
G_p	f = 160 MHz	P_{IN} = 5.0 W	V_{CE} = 13.6 V	9	---	---	dB
Cob	V_{CE} = 12.5V	f = 1 MHz		---	95	---	pf

IMPEDANCE DATA

FREQ	Z _{IN} (Ω)	Z _{CL} (Ω)
160 MHz	1.0 + j0.4	2.3 + j0.1

P_{IN} = 3.0 W
V_{CE} = 12.5V

MS1506

PACKAGE MECHANICAL DATA

